Application No. 10/825,871 Amdt. Dated November 15, 2005 Reply to Office Action of October 17, 2005

## Amendments to the Specification:

Please replace paragraph [0008] with the following amended paragraph:

energy which is inductively coupled inside the reactor dome. The antenna generates a high density, low energy plasma inside the chamber for etching metals, dielectrics and semiconductor materials. Auxiliary RF bias energy applied to the wafer support cathode controls the cathode sheath voltage and controls the ion energy independent of density. The RF energy inductively coupled to the dome creates a heat that must be moderated. The invention herein utilizes a temperature-controlled airflow to supply a continuously variable air temperature over a wide range of process conditions including idling.

Please delete the abstract and substitute therefor the new abstract in the following sheet: